SONY

ICX074AL

Diagonal 8mm (Type 1/2) Progressive Scan CCD Image Sensor with Square Pixel for EIA B/W Video Cameras

Description

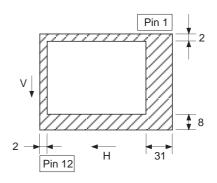
The ICX074AL is an interline CCD solid-state image sensor suitable for EIA black-and-white video cameras. Progressive scan allows all pixels signals to be output independently within approximately 1/60 second. This chip features an electronic shutter with variable charge-storage time which makes it possible to realize full-frame still image without mechanical shutter. Individual pixels in a square matrix make this device suitable for image input and processing applications.

High sensitivity and low dark current are achieved through the adoption of HAD (Hole-Accumulation Diode) sensors.

Features

- Progressive scan allows individual readout of the image signals from all pixels.
- High vertical resolution (480TV-lines) still picture without mechanical shutter.
- Square pixel unit cell
- VGA format-compatible
- High resolution, high sensitivity, low dark current
- Continuous variable-speed shutter
- Low smear
- Excellent antiblooming characteristics
- Reset gate: 5V drive (bias: no adjustment)

22 pin DIP (Cer-DIP)



Optical black position (Top View)

Device Structure

• Image size: Diagonal 8mm (Type 1/2)

• Number of effective pixels: $659 \text{ (H)} \times 494 \text{ (V)}$ approx. 330K pixels • Total number of pixels: $692 \text{ (H)} \times 504 \text{ (V)}$ approx. 350K pixels

Interline CCD image sensor

Chip size: 8.10mm (H) × 6.33mm (V)
 Unit cell size: 9.9μm (H) × 9.9μm (V)

• Optical black: Horizontal (H) direction: Front 2pixels, rear 31pixels

Vertical (V) direction: Front 8pixels, rear 2pixels

Number of dummy bits: Horizontal 16

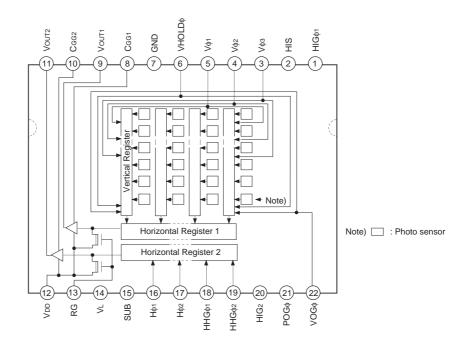
Vertical 5

• Substrate material: Silicon

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Block Diagram and Pin Configuration

(Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	HIGφ1	Test pin *2	12	Vdd	Supply voltage
2	HIS	Test pin *2	13	RG	Reset gate clock
3	Vфз	Vertical register transfer clock	14	VL	Protective transistor bias
4	Vф2	Vertical register transfer clock	15	SUB	Substrate (overflow drain)
5	Vф1	Vertical register transfer clock	16	Нф1	Horizontal register transfer clock
6	VHOLDφ	Vertical register final stage accumulation clock	17	Нф2	Horizontal register transfer clock
7	GND	GND	18	HHG _{\$1}	Inter-horizontal register transfer clock
8	CGG1	Output amplifier 1 gate *1 decoupling capacitor	19	HHG _{\$\psi_2\$}	Inter-horizontal register transfer clock
9	Vout1	Signal output 1	20	HIG ₂	Test pin *2
10	CGG2	Output amplifier 2 gate *1 decoupling capacitor	21	POGφ	Test pin *2
11	Vout2	Signal output 2	22	VOGφ	Vertical register final stage transfer clock

^{*1} DC bias is applied within the CCD, so that this pin should be grounded externally through a capacitance of 1μF or more.

^{*2} Regarding the test pins: apply the same voltage as the supply voltage to HIS, and ground HIG ϕ_1 , HIG2, and POG ϕ .

Absolute Maximum Ratings

	Item	Ratings	Unit	Remarks
Substrate voltage SUB – GN	ID	-0.3 to +55	V	
Cupply voltage	VDD, VOUT1, VOUT2, HIS, CGG1, CGG2 – GND	-0.3 to +18	V	
Supply voltage	VDD, VOUT1, VOUT2, HIS, CGG1, CGG2 – SUB	-55 to +10	V	
Clock input voltage	Vφ1, Vφ2, Vφ3, VHOLDφ, VOGφ – GND	-15 to +20	V	
Clock input voltage	Vφ1, Vφ2, Vφ3, VHOLDφ, VOGφ – SUB	to +10	V	
Voltage difference between	to +15	V	*1	
Voltage difference between	to +17	V		
Hφ1, Hφ2 – VOGφ	-17 to +17	V		
Hφ1, Hφ2 – GND		-10 to +15	V	
Hφ1, Hφ2 – SUB		-55 to +10	V	
VL – SUB		-65 to +0.3	V	
Vφ2, Vφ3, Vdd, Vout1, Vout2,	HIS, HIGφ1, HIG2, POGφ – VL	-0.3 to +27.5	V	
RG – GND		-0.3 to +22.5	V	
Vφ1, CgG1, CgG2, Hφ1, Hφ2, F	-0.3 to +17.5	V		
Storage temperature	-30 to +80	°C		
Operating temperature		-10 to +60	°C	

^{*1 +27}V (Max.) when clock width < 10µs, clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	Vdd	14.55	15.0	15.45	V	
Substrate voltage adjustment range	VsuB	9.0		18.5	V	*1
Substrate voltage adjustment precision		Indicated voltage –0.1	Indicated voltage	Indicated voltage +0.1	V	
Protective transistor bias	VL					

DC Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		10		mA	
Input current	lin1			1	μΑ	*3
Input current	I _{IN2}			10	μΑ	*4

^{*1} Indications of substrate voltage (Vsub) setting value

The setting value of the substrate voltage is indicated on the back of image sensor by a special code. Adjust the substrate voltage (Vsub) to the indicated voltage.

Integer portion Decimal portion

The integer portion of the code and the actual value correspond to each other as follows.

Integer portion of code	9	Α	С	d	Е	f	G	h	J	K
Value	9	10	11	12	13	14	15	16	17	18

<Example> "A5" \rightarrow Vsub = 10.5V.

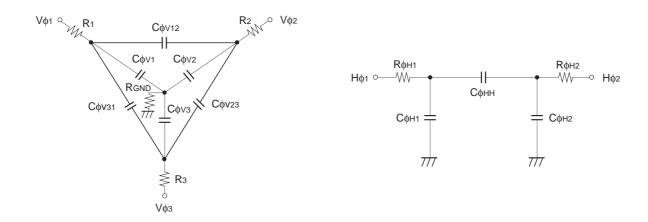
- *2 VL setting is the VvL voltage of the vertical transfer clock waveform, or the same power supply as the VL power supply for the V driver should be used.
- *3 (1) Current to each pin when 18V is applied to VDD, VOUT1, VOUT2, HIS, RG, CGG1, CGG2, GND and SUB pins, while pins that are not tested are grounded.
 - (2) Current to each pin when 20V is applied sequentially to $V\phi_1$, $V\phi_2$ and $V\phi_3$ pins, while pins that are not tested are grounded. However, 20V is applied to SUB pin.
 - (3) Current to each pin when 15V is applied sequentially to RG, $H\phi_1$ and $H\phi_2$ pins, while pins that are not tested are grounded. However, 15V is applied to SUB pin.
 - (4) Current to V_L pin when 25V is applied to Vφ₂, Vφ₃, POGφ, HIGφ₁, HIG₂, V_{DD}, V_{OUT1} and V_{OUT2} pins or when, 15V is applied to Vφ₁, VHOLDφ, VOGφ, C_{GG1}, C_{GG2}, Hφ₁, Hφ₂, HHGφ₁ and HHGφ₂ pins, while V_L pin is grounded. However, GND and SUB pins are left open.
 - (5) Current to GND pin when 20V is applied to the RG pin and the GND pin is grounded.
- *4 Current to SUB pin when 55V is applied to SUB pin, while all pins that are not tested are grounded.

Clock Voltage Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.55	15.0	15.45	V	1	
	VvH02	-0.05	0	0.05	V	2	VvH = VvH02
	Vvh1, Vvh2, Vvh3	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3	-8.0	-7.5	-7.0	V	2	VvL = (VvL01 + VvL03)/2
Mant's alternation along	Vφv	6.8	7.5	8.05	V	2	$V\phi V = VVHN - VVLN (n = 1 to 3)$
Vertical transfer clock voltage	I Vvl1 – Vvl3 I			0.1	V	2	
J	Vvнн			0.5	V	2	High-level coupling
	Vvhl			0.5	V	2	High-level coupling
	Vvlh			0.5	V	2	Low-level coupling
	Vvll			0.5	V	2	Low-level coupling
Horizontal transfer	Vфн	4.75	5.0	5.75	V	3	
clock voltage	VHL	-0.05	0	0.05	V	3	
	Vørg	4.5	5.0	5.5	V	4	Input through 0.01µF capacitance
Reset gate clock voltage	Vrglh – Vrgll			0.8	V	4	Low-level coupling
· · · · · · · · · · · · · · · · · · ·	Vrgh	V _{DD} +0.4	V _{DD} +0.6	V _{DD} +0.8	V	4	
Substrate clock voltage	Vфsuв	21.5	22.5	23.5	V	5	
Vertical final stage accumulation clock voltage	Vvholdh, Vvogh	-0.05	0	0.05	V	6	
transfer clock voltage	Vvholdl, Vvogl	-8.0	-7.5	-7.0	V	6	
	Vннg1н, Vннg2н	4.75	5.0	5.25	V	7	
Inter-horizontal register transfer clock voltage	VHHG1L, VHHG2L	-8.0	-7.5	-7.0	V	7	
	VHHG1M, VHHG2M	-0.05	0	0.05	V	7	

Clock Equivalent Circuit Constant

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
	Сф∨1		3300		pF	
Capacitance between vertical transfer clock and GND	Сф∨2		4700		pF	
olook and SNB	Сфvз		4700		pF	
	СфV12		1000		pF	
Capacitance between vertical transfer clocks	Сф∨23		22		pF	
Olooks	Сф∨31		100		pF	
Capacitance between vertical final stage accumulation clock and GND	Сфуногр		19		pF	
Capacitance between vertical final stage transfer clock and GND	Сфуос		12		pF	
Capacitance between inter-horizontal	Сфннg1		23		pF	
register transfer clock and GND	Сфннд2		19		pF	
Capacitance between horizontal transfer	Сфн1		60		pF	
clock and GND	Сфн2		69		pF	
Capacitance between horizontal transfer clocks	Сфнн		40		pF	
Capacitance between reset gate clock and GND	Сфяд		9		pF	
Capacitance between substrate clock and GND	Сфѕив		400		pF	
Vertical transfer clock series resistor	R1, R2, R3		10		Ω	
Vertical transfer clock ground resistor	RGND		15		Ω	
Havizantal transfer alask parios resistar	R фн1		24		Ω	
Horizontal transfer clock series resistor	Р фн2		30		Ω	

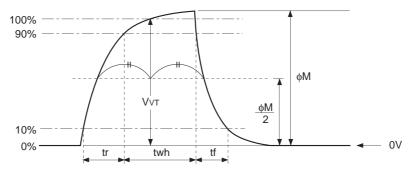


Vertical transfer clock equivalent circuit

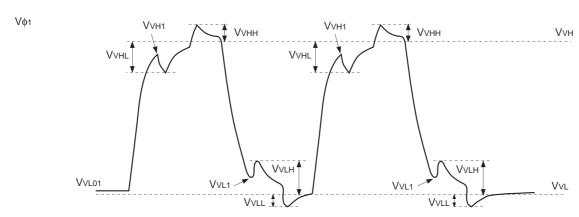
Horizontal transfer clock equivalent circuit

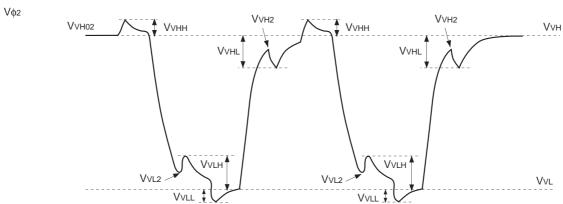
Drive Clock Waveform Conditions

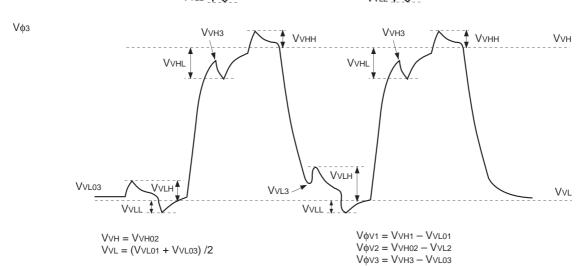
(1) Readout clock waveform



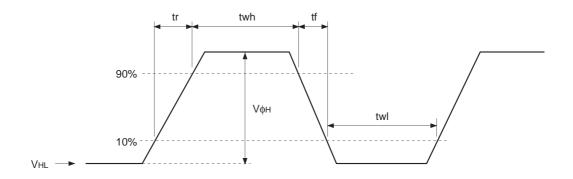
(2) Vertical transfer clock waveform



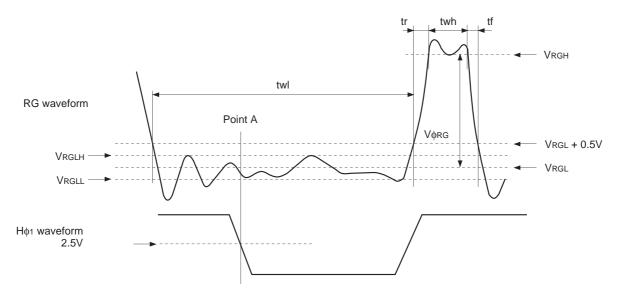




(3) Horizontal transfer clock waveform



(4) Reset gate clock waveform



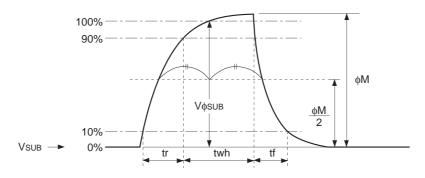
VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG. In addition, VRGL is the average value of VRGLH and VRGLL.

$$V_{RGL} = (V_{RGLH} + V_{RGLL})/2$$

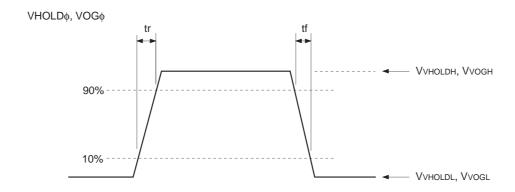
Assuming VRGH is the minimum value during the interval twh, then:

$$V\phi RG = VRGH - VRGL$$

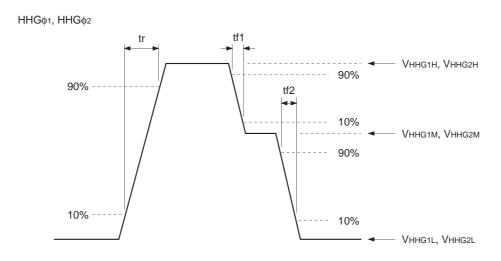
(5) Substrate clock waveform



(6) Vertical final stage accumulation clock waveform · Vertical final stage transfer clock waveform



(7) Inter-horizontal register transfer clock waveform



Clock Switching Characteristics

	Item	Symbol		twh			twl			tr		tf,	tf1, t	f2	Unit	Remarks
	пеш	Symbol	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Offic	Remarks
R	eadout clock	Vт	2.3	2.5						0.5			0.5		μs	During readout
1	ertical transfer ock	Vф1, Vф2, Vф3										15		350	ns	*1
clock	During imaging	Нф1	24	29		26	31			10	17.5		10	17.5		*2
Horizontal transfer clock	During imaging	Нф2	26	31		24	29			10	15		10	15	ns	_
ontal tr	During parallel-	Нф1								0.01			0.01		μs	
Horiz	serial conversion	Нф2								0.01			0.01		μδ	
R	eset gate clock	φRG	11	13			64			2			2		ns	
Sı	ubstrate clock	фѕив	1.6	1.9							0.5			0.5	μs	During drain charge
	ertical final stage	VHOLDφ								20			20		ns	
	ccumulation/ ansfer clock	VOGφ								20			20		ns	
	ter-horizontal	HHG _{\$1}								20			20		ns	
	gister transfer ock	HHGφ2								20			20		ns	

^{*1} When vertical transfer clock driver CXD1268M is used.

^{*2} tf \geq tr - 2ns, and the cross-point voltage (VcR) for the H ϕ 1 rising side of the H ϕ 1 and H ϕ 2 waveforms must be at least 2.5V.

Item	Symbol		two		Unit	Remarks	
Item	Symbol	Min.	Тур.	Мах.	Offic	Remarks	
Horizontal transfer clock	Нф1, Нф2	24	29		ns	*3	

 $^{^{*3}}$ The overlap period for twh and twl of horizontal transfer clocks $H\phi_1$ and $H\phi_2$ is two.

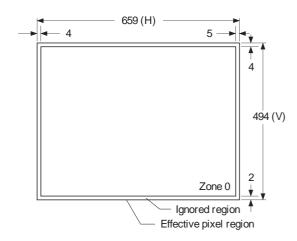
Image Sensor Characteristics

 $(Ta = 25^{\circ}C)$

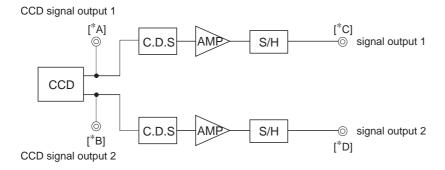
Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S		350		mV	1	
Saturation signal	Vsat	500			mV	2	Ta = 60°C
Smear	Sm		0.002	0.007	%	3	
Video signal shading	SH			25	%	4	Zone 0
Dark signal	Vdt			2	mV	5	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	6	Ta = 60°C
Lag	Lag			0.5	%	7	
Uniformity between output channels	ΔV			3	%	8	

Note) All the characteristic data of this image sensor was yielded when the sensor was operated in the 1/60s interlaced mode.

Zone Definition of Video Signal Shading



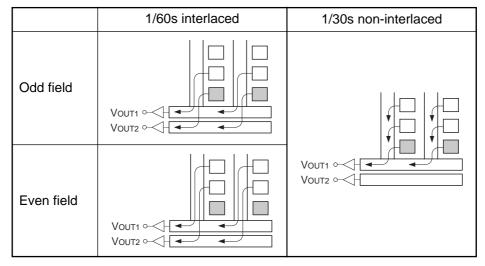
Measurement System



Note) Adjust the amplifier gain so that the gain between [*A] and [*C], and between [*B] and [*D] equals 1.

Readout modes

The output methods for the two readout modes indicated below are now described.



1. 1/60s interlaced

In this mode, the signals are output in a 1/60s period using the two output pins (Vout1, Vout2).

The signals from two adjacent horizontal lines are simultaneously output from the respective output pins.

The lines output from the output pins are changed over with each field. The Vout1 signal after it has passed through the CDS and other external circuits or the signal produced by adding the Vout1 and Vout2 signals accommodate interlaced scanning.

2. 1/30s non-interlaced

In this mode, the signals are output in a 1/30s period using only one output pin (VouT1).

Unlike the 1/60s interlaced mode described above, the external circuit can be simplified. The imaging characteristics also differ from those of the other modes.

Image Sensor Characteristics Measurement Method

Measurement conditions

1) In the following measurements, the substrate voltage is set to the value indicated on the device, and the device drive conditions are at the typical values of the bias and clock voltage conditions.

- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output and the value measured at point [*A] in the measurement system is used.
- 3) In the following measurements, this image sensor is operated in 1/60s interlaced mode.

O Definition of standard imaging conditions

1) Standard imaging condition I:

Use a pattern box (luminance 706cd/m^2 , color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.00mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.00mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen and substitute the value into the following formula.

$$S = Vs \times \frac{250}{60} \text{ [mV]}$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with average value of signal output, 150mV, measure the minimum value of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with average value of signal output, 150mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value VSm [mV] of the signal output and substitute the value into the following formula.

$$Sm = \frac{VSm}{150} \times \frac{1}{500} \times \frac{1}{10} \times 100 \text{ [\%] (1/10V method conversion value)}$$

4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 150mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

$$SH = (Vmax - Vmin)/150 \times 100 [\%]$$

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

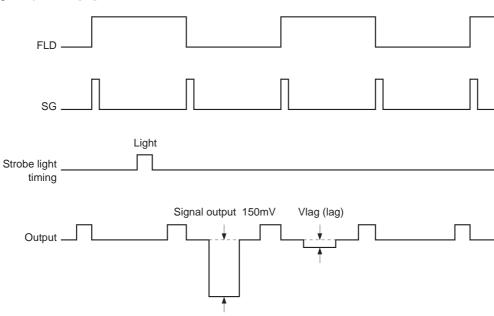
After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

$$\Delta Vdt = Vdmax - Vdmin [mV]$$

7. Lag

Adjust the signal output value generated by strobe light to 150mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

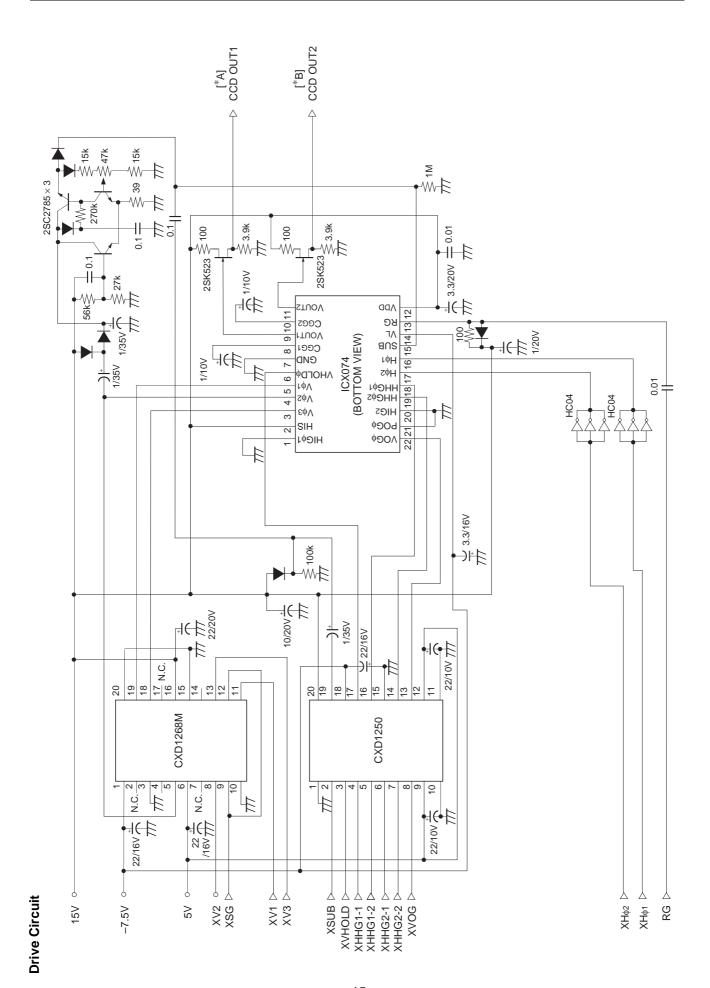
$$Lag = (Vlag/150) \times 100 [\%]$$



8. Uniformity between output channels

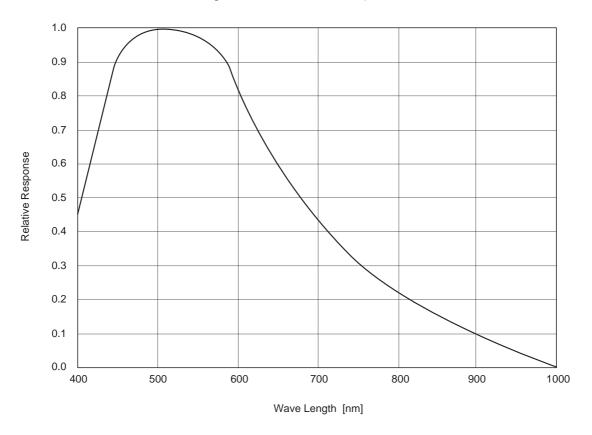
Set to standard imaging condition I. Measure the signals at signal output 1 (V1) and at signal output 2 (V2), and substitute the values into the following formula.

$$\Delta V = \frac{1 \text{ V2} - \text{V1I}}{\text{V1}} \times 100 \text{ [\%]}$$



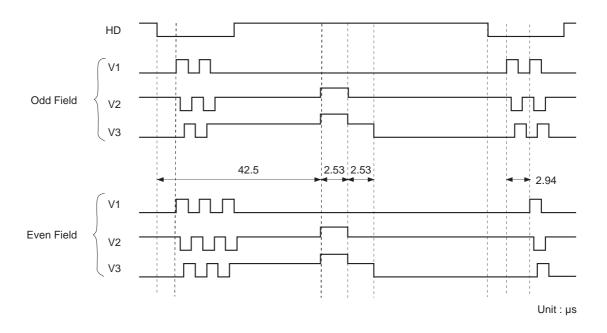
Spectral Sensitivity Characteristics

(includes lens characteristics, excludes light source characteristics)

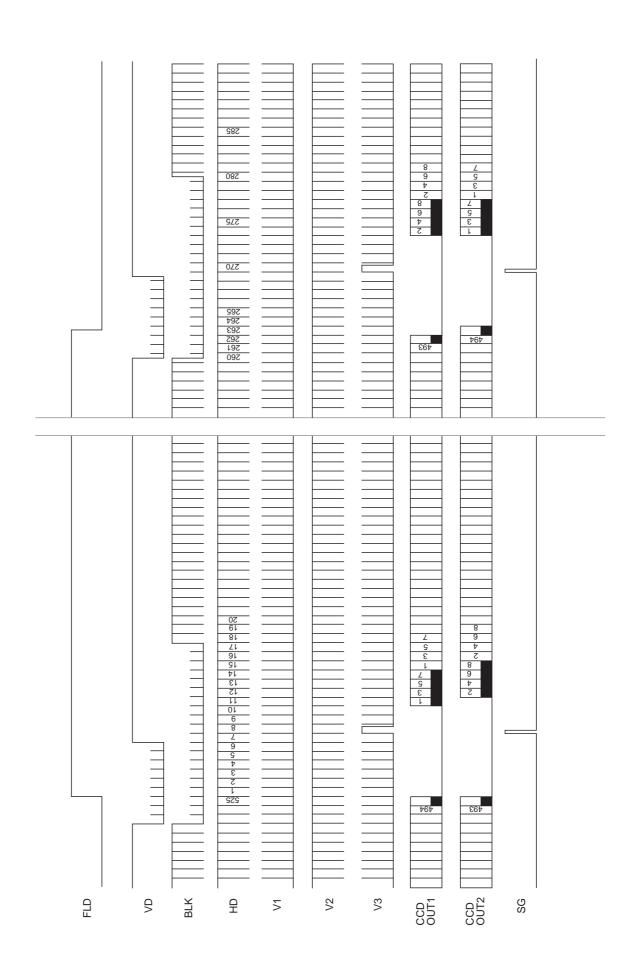


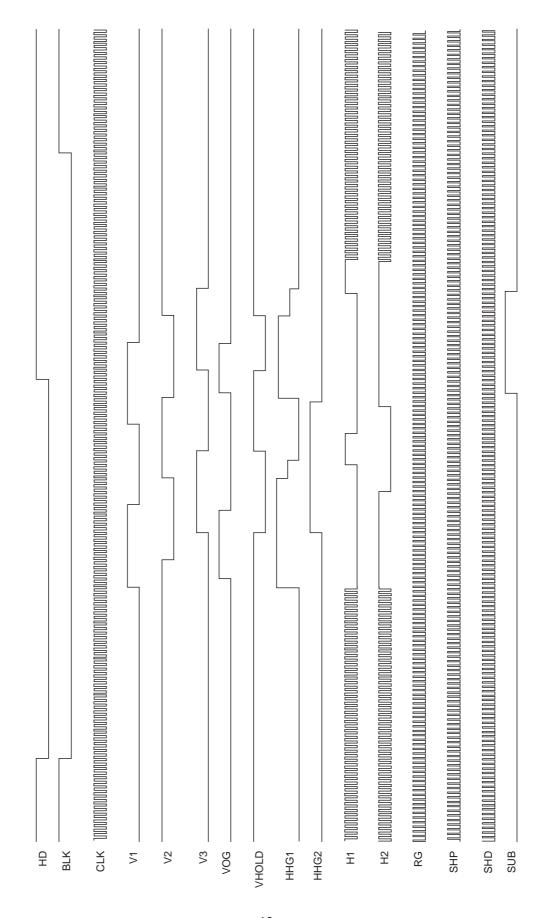
Sensor Readout Clock Timing Chart

1/60s interlaced mode



Drive Timing Chart (Vertical Sync) 1/60s interlaced mode





Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

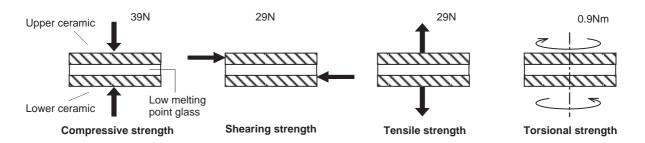
3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.

4) Installing (attaching)

a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)



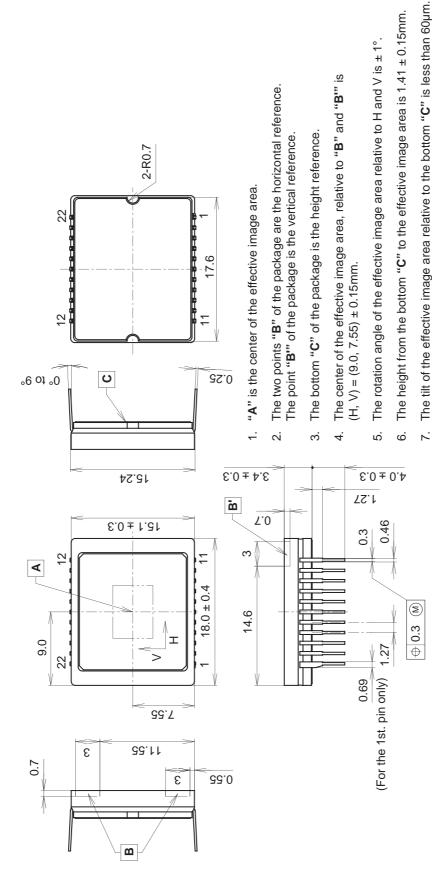
b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the ceramic portions. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.

- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to other locations as a precaution.
- d) The upper and lower ceramic are joined by low melting point glass. Therefore, care should be taken not to perform the following actions as this may cause cracks.
 - Applying repeated bending stress to the outer leads.
 - Heating the outer leads for an extended period with a soldering iron.
 - Rapidly cooling or heating the package.
 - Applying any load or impact to a limited portion of the low melting point glass using tweezers or other sharp tools.
 - Prying at the upper or lower ceramic using the low melting point glass as a fulcrum.
 Note that the same cautions also apply when removing soldered products from boards.
- e) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)

5) Others

- a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.

22pin DIP (600mil)



PACKAGE STRUCTURE

The thickness of the cover glass is 0.75mm, and the refractive index is 1.5.

ထ် တ်

The notches on the bottom must not be used for reference of fixing.

PACKAGE MATERIAL	Cer-DIP
LEAD TREATMENT	TIN PLATING
LEAD MATERIAL	42 ALLOY
PACKAGE WEIGHT	2.6g

- 21	_